TOSHIBA PHOTOCOUPLER GaA&As IRED & PHOTO IC

TLP2631

ISOLATED LINE RECEIVER

SIMPLEX / MULTIPLEX DATA TRANSMISSION

COMPUTER-PERIPHERAL INTERFACE

MICROPROCESSOR SYSTEM INTERFACE

DIGITAL ISOLATION FOR A/D, D/A CONVERSION

The TOSHIBA TLP2631 dual photocoupler consists of a pair of GaAtAs light emitting diode and integrated high gain, high speed photodetector.

This unit is 8-lead DIP.

The output of the detector circuit is an open collector, Schottky clamped transistor.

A Faraday shield integrated on the photodetector chip reduces the effects of capacitive coupling between the input LED emitter and the high gain stages of the detector. This provides an effective common mode transient immunity of $1000V/\mu s$.

- Input Current Threshold : $I_F = 5mA(MAX.)$
- : 10MBd (TYP.) Switching Speed
- Common Mode Transient Immunity $\pm 1000 V / \mu s$ (MIN.)
- Guaranteed Performance Over Temperature : 0~70°C
- Isolation Voltage : 2500V_{rms} (MIN.)
- **UL** Recognized

: UL1577, File No. E67349

TRUTH TABLE (Positive Logic)

INPUT	OUTPUT
Н	L
L	Н

A 0.01 to $0.1 \mu F$ bypass capacitor must connected between pins 8 and 5 (See Note 1).



 2.54 ± 0.25

<u>7</u> 6

고 3

9.66 ± 0.25

3.65 +0.15

2.5MIN.

11-10C4

PIN CONFIGURATION (TOP VIEW)

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0.5 ± 0







Unit in mm

7.62 ± 0.25

0.25 +0.1

7.85~8.80

11-10C4

	CHARACTERISTIC	SYMBOL	RATING	UNIT
			-	01111
	Foward Current (Each Channel)	$I_{\rm F}$	20	mA
LED	Pulse Forward Current (Each Channel)*	IFP	30	mA
	Reverse Voltage (Each Channel)	VR	5	v
	Output Current (Each Channel)	IO	16	mA
OR	Output Voltage (Each Channel)	VO	$-0.5 \sim 7$	V
DETECTOR	Supply Voltage (1 Minute Maximum)	V _{CC}	7	v
	Output Collector Power Dissipation (Each Channel)	PO	40	mW
Operating Temperature Range		$\mathrm{T_{stg}}$	$-55 \sim 125$	°C
St	orage Temperature Range	T _{opr}	$-40 \sim 85$	°C
Lead Soldering Temperature (10s)**		T _{sol}	260	°C
	olation Voltage .C, 1min., R.H.≦60%, Note 3)	ΒV _S	2500	Vrms

MAXIMUM RATINGS (No derating required up to 70°C)

* t \leq 1 msec Duration.

** 2mm below seating plane.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input Current, Low Level, Each Channel	$I_{\rm FL}$	0	_	250	$\mu \mathbf{A}$
Input Current, High Level, Each Channel	I_{FH}	6.3*		20	mA
Supply Voltage, Output	V _{CC}	4.5	5	5.5	V
Fan Out (TTL Load, Each Channel)	N		_	8	
Operating Temperature	T _{opr}	0	_	70	°C

* 6.3mA is a guard banded value which allows for at least 20% CTR degradation. Initial input current threshold value is 5.0mA or less.

ELECTRICAL CHARACTERISTICS ($1a = 0 \sim 70^{\circ}$ C, Unless otherwise noted)							
CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.*	MAX.	UNIT
Input Forward Voltage (Each Channel)	$V_{\mathbf{F}}$	I _F =10mA, Ta=25°C		_	1.65	1.75	v
Input Diode Temperature Coefficient (Each Channel)	$\Delta V_{\rm F} / \Delta T_{\rm A}$	$I_{\rm F} = 10 {\rm mA}$		_	-2.0	_	mV/°C
Input Reverse Breakdown Voltage (Each Channel)	BVR	I _R =10µA, Ta=25°C		5	_	_	v
Input Capacitance (Each Channel)	C_{T}	$V_F=0$, f=1MHz		_	45	_	pF
High Level Output Current (Each Channel)	IOH	$V_{CC} = 5.5V, V_O = 5.5V$ $I_F = 250 \mu A$		_	1	250	$\mu \mathbf{A}$
Low Level Output Voltage (Each Channel)	V _{OL}	V _{CC} =5.5V, I _F =5mA I _{OL} (Sinking) =13mA		_	0.4	0.6	v
High Level Supply Current (Both Channels)	ICCH	$V_{CC} = 5.5V, I_F = 0$		_	14	30	mA
Low Level Supply Current (Both Channels)	ICCL	V _{CC} =5.5V, I _F =10mA		_	24	38	mA
Isolation Voltage	RS	Vg=500V, R.H. \leq 60%(N	Note 3)	5×10^{10}	10^{14}	_	Ω
Capacitance (Input-Output)	CS	f=1MHz (1	Note 3)	_	0.6	_	pF
Input-Input Leakage Current	II-I	R.H. $\leq 60\%$, t=5s V _{I-I} =500V (N	Note 6)	_	0.005		$\mu \mathbf{A}$
Resistance (Input-Input)	R _{I-I}	V _{I-I} =500V (1	Note 6)	_	1011	_	Ω
Capacitance (Input-Input)	C _{I-I}	f=1MHz (N	Note 6)	_	0.25	_	pF

ELECTRICAL	CHARACTERISTICS (Ta = $0 \sim 70^{\circ}$ C,	Unless	otherwise	noted)
LECINCAL		0111035	0111111111	noted)

* All typical values are at $V_{\mbox{CC}}{=}5\mbox{V},\,\mbox{Ta}{=}25\mbox{°C}.$

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	ТҮР.	MAX.	UNIT
Propagation Delay Time to Low Output Level	$t_{ m pHL}$	1	$I_F=0 \rightarrow 7.5 \text{mA}, R_L=350\Omega$ $C_L=15 \text{pF}$ (Each Channel)	_	60	75	ns
Propagation Delay Time to High Output Level	^t pLH	1	I _F =7.5mA \rightarrow 0, R _L =350Ω C _L =15pF (Each Channel)	_	60	75	ns
Output Rise time, Output Fall time (10~90%)	t _r , t _f	1	$I_F = 0 \rightleftharpoons 7.5 \text{mA}, R_L = 350\Omega$ $C_L = 15 \text{pF}$ (Each Channel)	_	30	_	ns
Common Mode Transient Immunity at High Output Level	СМ _Н	2	$I_{F}=0, R_{L}=350\Omega$ $V_{CM}=400V,$ $V_{O} (MIN.)=2V$ (Each Channel, Note 4)	1000	10000	_	V/μs
Common Mode Transient Immunity at Low Output Level	CM_L	2	$I_{F}=7.5\text{mA}, R_{L}=350\Omega$ $V_{CM}=400V$ $V_{O} (MAX.)=0.8V$ (Each Channel, Note 5)	-1000	-10000		V/μs

SWITCHING CHARACTERISTICS (Ta = 25° C, V_{CC} = 5V)

(Note 1) 2mm below seating plane

- (Note 2) The V_{CC} supply voltage to each TLP2631 isolator must be bypassed by a 0.01μ F capacitor or larger. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close as possible to the package V_{CC} and GND pins each device.
- (Note 3) Device considered a two-terminal device : Pins 1, 2, 3 and 4 shorted together, and Pins 5, 6, 7 and 8 shorted together.
- (Note 4) $CM_H \cdot The maximum tolerable rate of rise of the common mode voltage to ensure the output will remain in the high state (i.e., <math>V_{OUT}>2.0V$). Measured in volts per microsecond (V/ μ s).

Volts/microsecond can be translated to sinusoidial voltages :

$$V/\mu s = \frac{(dVCM)}{dt}$$
 Max.=f_{CM} V_{CM} (p.p.)

Example :

 $V_{CM}\!=\!319Vpp$ when $f_{CM}\!=\!1MHz$ using CM_L and $CM_H\!=\!1000V\,/\,\mu s$ data sheet specified minimum.

- (Note 5) $CM_L \cdot The maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the low output state (i.e., <math>V_{OUT} > 0.8V$). Measured in volts per microsecond (V/ μ s).
- (Note 6) Measured between pins 1 and 2 shorted together, and pins 3 and 4 shorted together.

TEST CIRCUIT 1. tpHL and tpLH



TEST CIRCUIT 2. Transient Immunity and Typical Waveforms.



 * C_L is approximately 15pF which includes probe and stray wiring capacitance.

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